



30V N&P-Channel Trench Power MOSFET

General Description

The SJP30NP360 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as $\pm 4.5V$. This device is suitable for use as a wide variety of applications.

Features

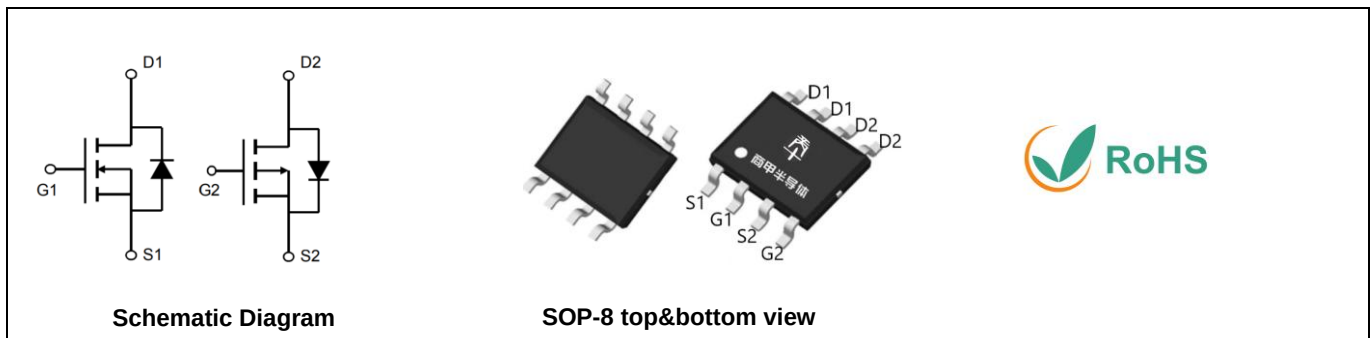
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

- Battery Protection
- Power Management
- Load Switch

Key Performance Parametes

Parameter	Value	Value	Unit
V_{DS}	30	-30	V
$R_{DS(ON_TYP)}$	9.7	24.4	m Ω
I_D	11.3	-7.1	A
Q_G	14	16	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJP30NP360	SJP30NP360	SOP-8	Tape	\	\	4000 Pcs

Table 1. Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	N Limit	P Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	± 20	V
I_D	Drain Current-Continuous($T_A=25^\circ\text{C}$)	11.3	-7.1	A
	Drain Current-Continuous($T_A=100^\circ\text{C}$)	7	-4.5	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	45.2	-28.4	A
P_D	Maximum Power Dissipation($T_A=25^\circ\text{C}$)	2.5	2.5	W
	Maximum Power Dissipation($T_A=100^\circ\text{C}$)	1	1	W
E_{AS}	Avalanche energy (Note 2)	42	42	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150		$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	N Max	P Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient	51	51	$^\circ\text{C/W}$



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Table 3. N-Channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =30V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0		2.5	V
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A		10		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =5A T _J =25℃		9.7	12.1	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =4A T _J =25℃		15.8	21	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz		757		pF
C _{oss}	Output Capacitance			91		pF
C _{rss}	Reverse Transfer Capacitance			75		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		1.1		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =3Ω, R _{GEN} =3Ω		4.5		nS
t _r	Turn-on Rise Time			2.5		nS
t _{d(off)}	Turn-Off Delay Time			14.5		nS
t _f	Turn-Off Fall Time			3.5		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =5A		14		nC
Q _{gs}	Gate-Source Charge			2		nC
Q _{gd}	Gate-Drain Charge			3		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				11.3	A
V _{SD}	Forward on Voltage ^(Note 3)	V _{GS} =0V, I _S =5A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =5A, dI/dt=500A/μs		10		ns
Q _{rr}	Reverse Recovery Charge	I _F =5A, dI/dt=500A/μs		5		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

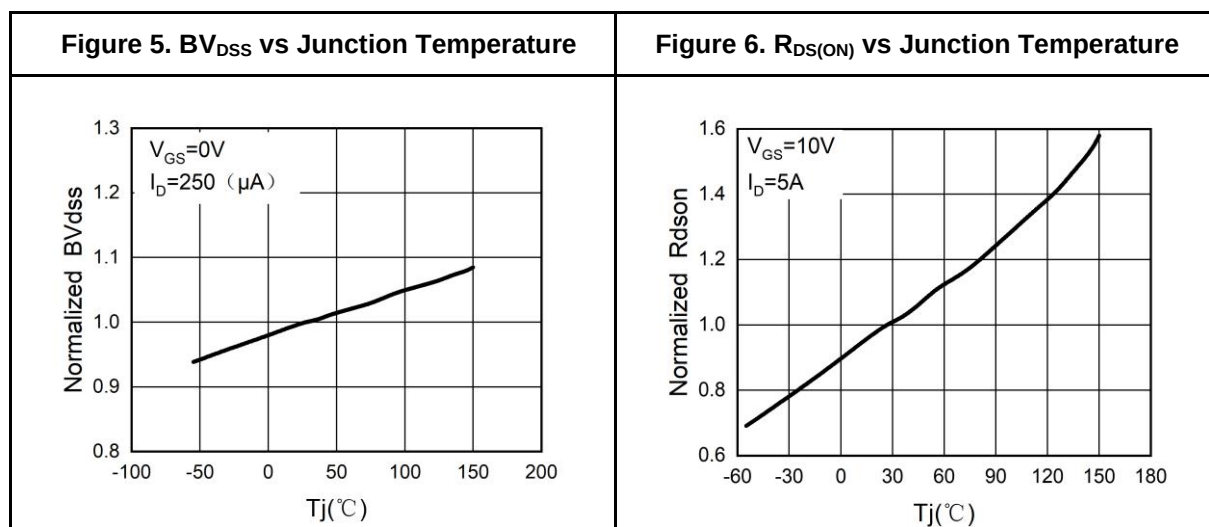
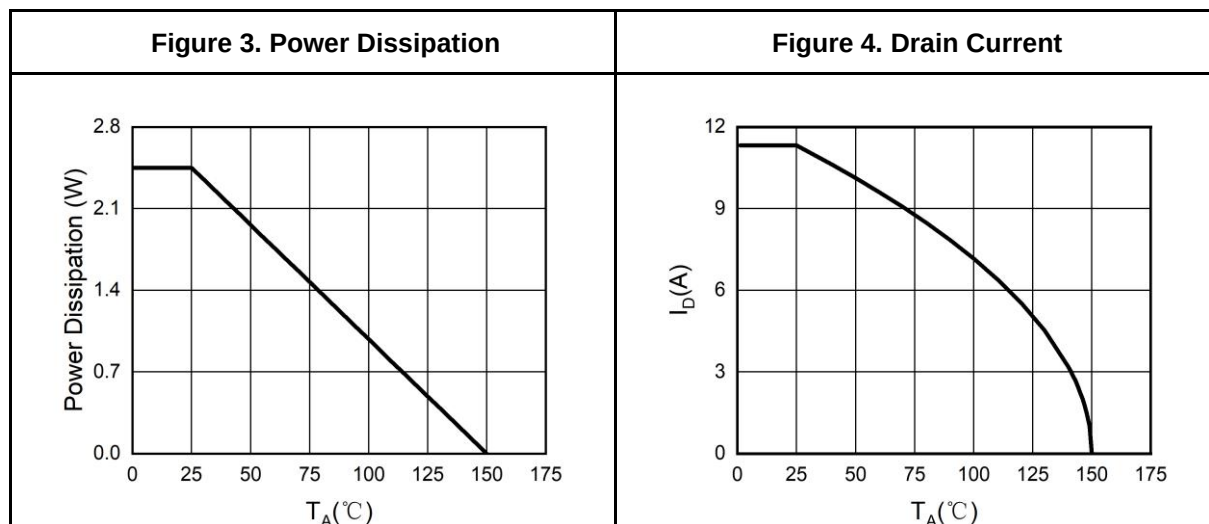
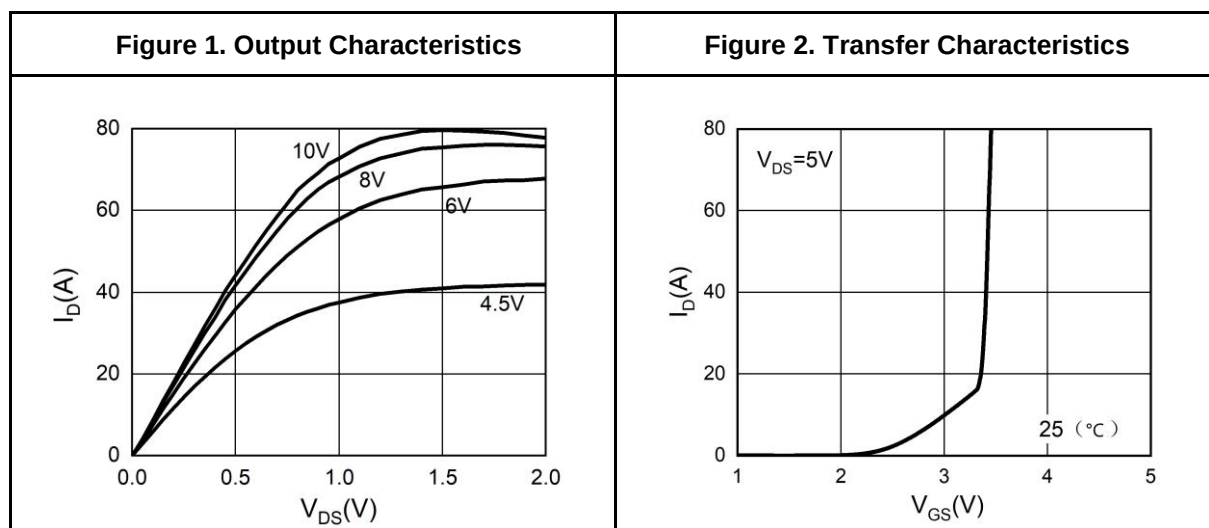
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DS}=30V, V_{GS}=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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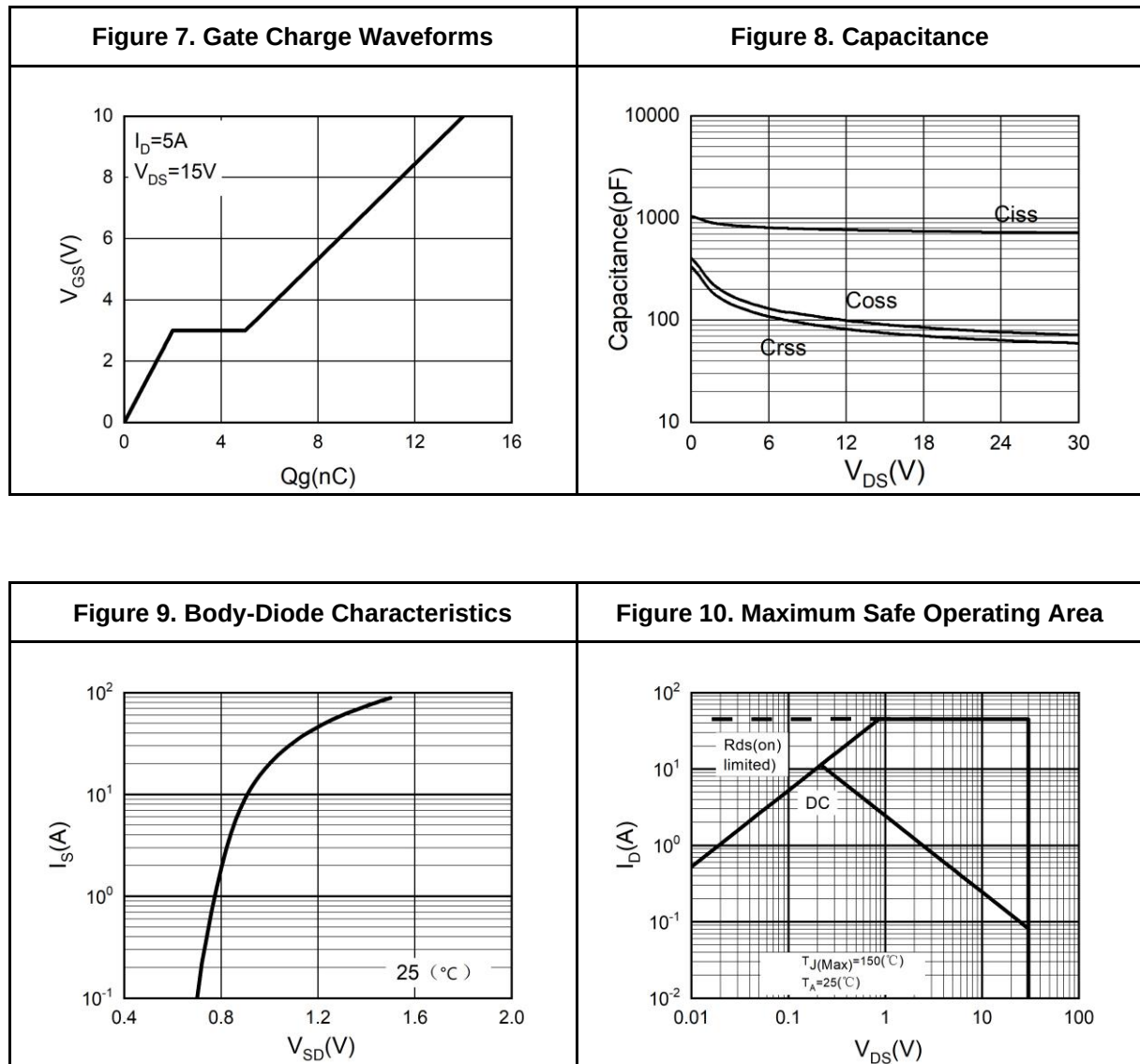
N-Channel Typical Electrical And Thermal Characteristics (Curves)





30V N&P-Channel Trench Power MOSFET

N-Channel Typical Electrical And Thermal Characteristics (Curves)





30V N&P-Channel Trench Power MOSFET

Table 4. P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =25℃			-1	μA
		V _{DS} =-30V, V _{GS} =0V T _J =125℃			-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1		-2.5	V
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-3A		7.6		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-3A T _J =25℃		24.4	30.5	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-2A T _J =25℃		31	41.2	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V,V _{GS} =0V, f=1.0MHz		718		pF
C _{oss}	Output Capacitance			95		pF
C _{rss}	Reverse Transfer Capacitance			80		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		5.7		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =5Ω, R _{GEN} =3Ω		7.5		nS
t _r	Turn-on Rise Time			5.5		nS
t _{d(off)}	Turn-Off Delay Time			19		nS
t _f	Turn-Off Fall Time			7		nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-3A		16		nC
Q _{gs}	Gate-Source Charge			2		nC
Q _{gd}	Gate-Drain Charge			4		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				-7.1	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =-3A			-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-3A, dI/dt=500A/μs		15		ns
Q _{rr}	Reverse Recovery Charge	I _F =-3A, dI/dt=500A/μs		10		nC

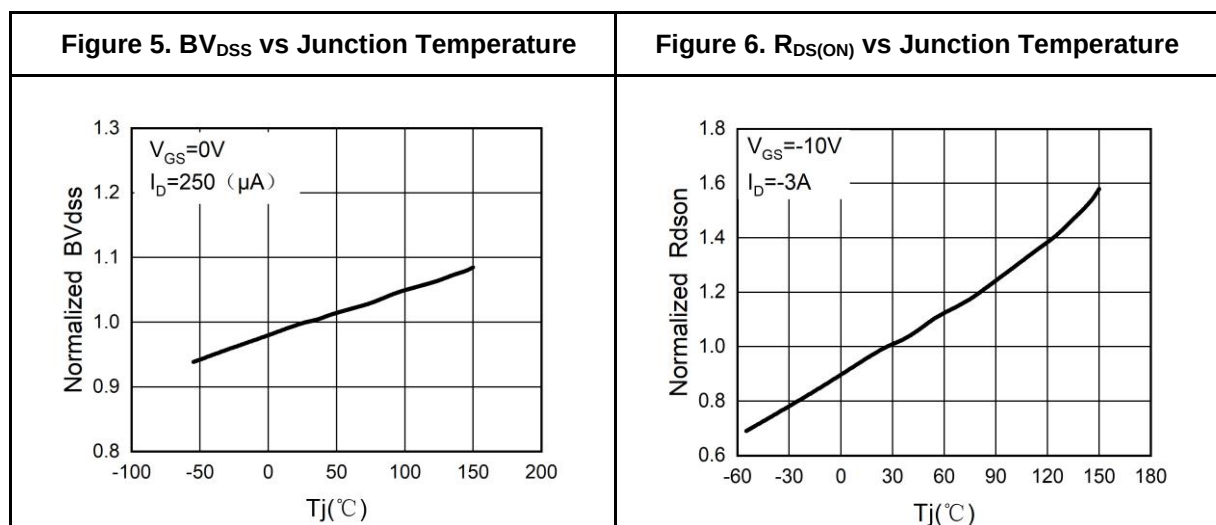
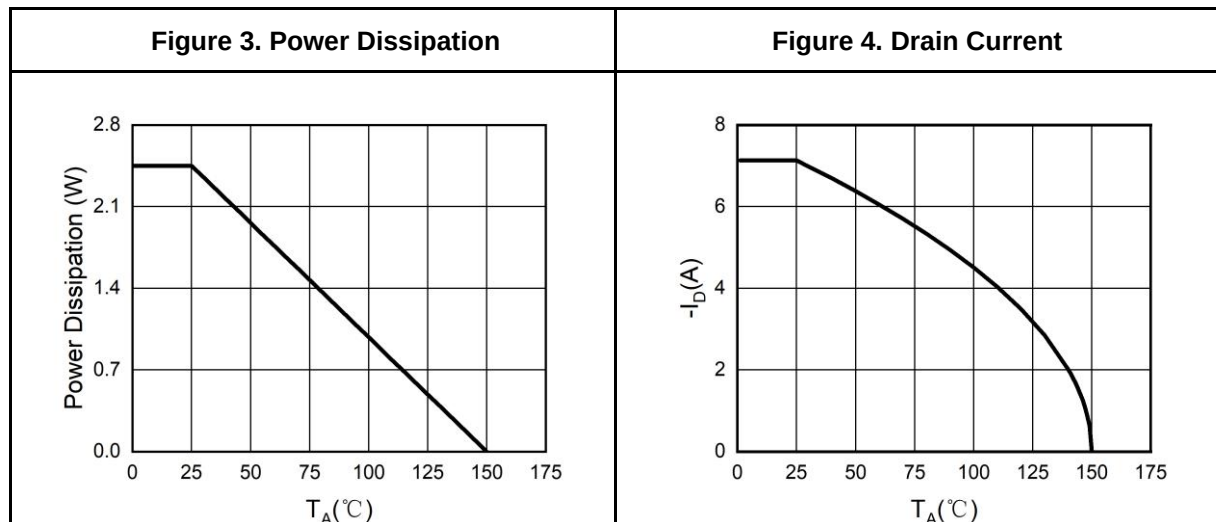
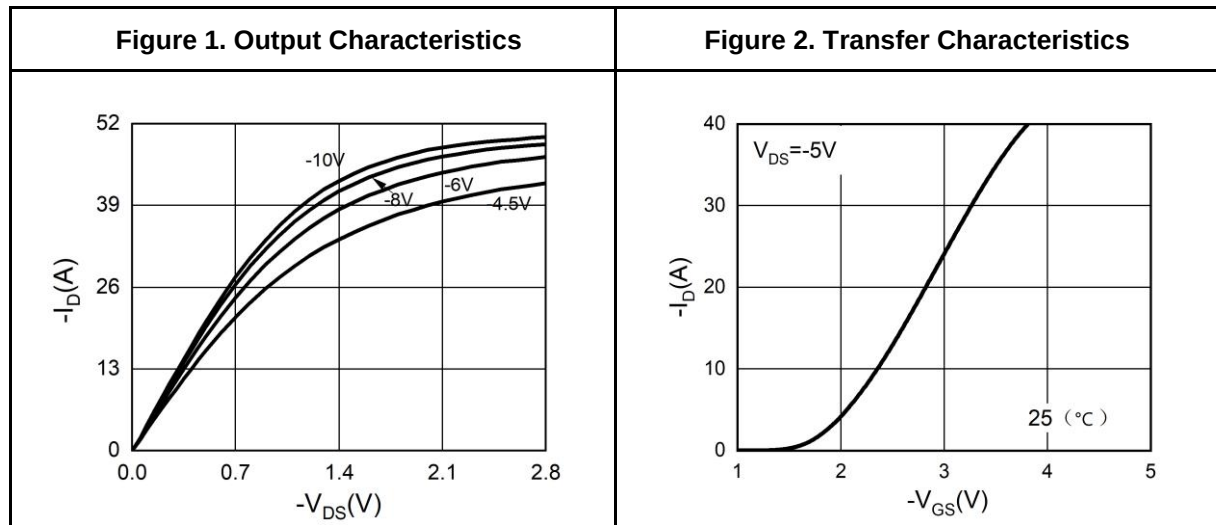
Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition: $T_J=25^\circ\text{C}, V_{DD}=-30V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



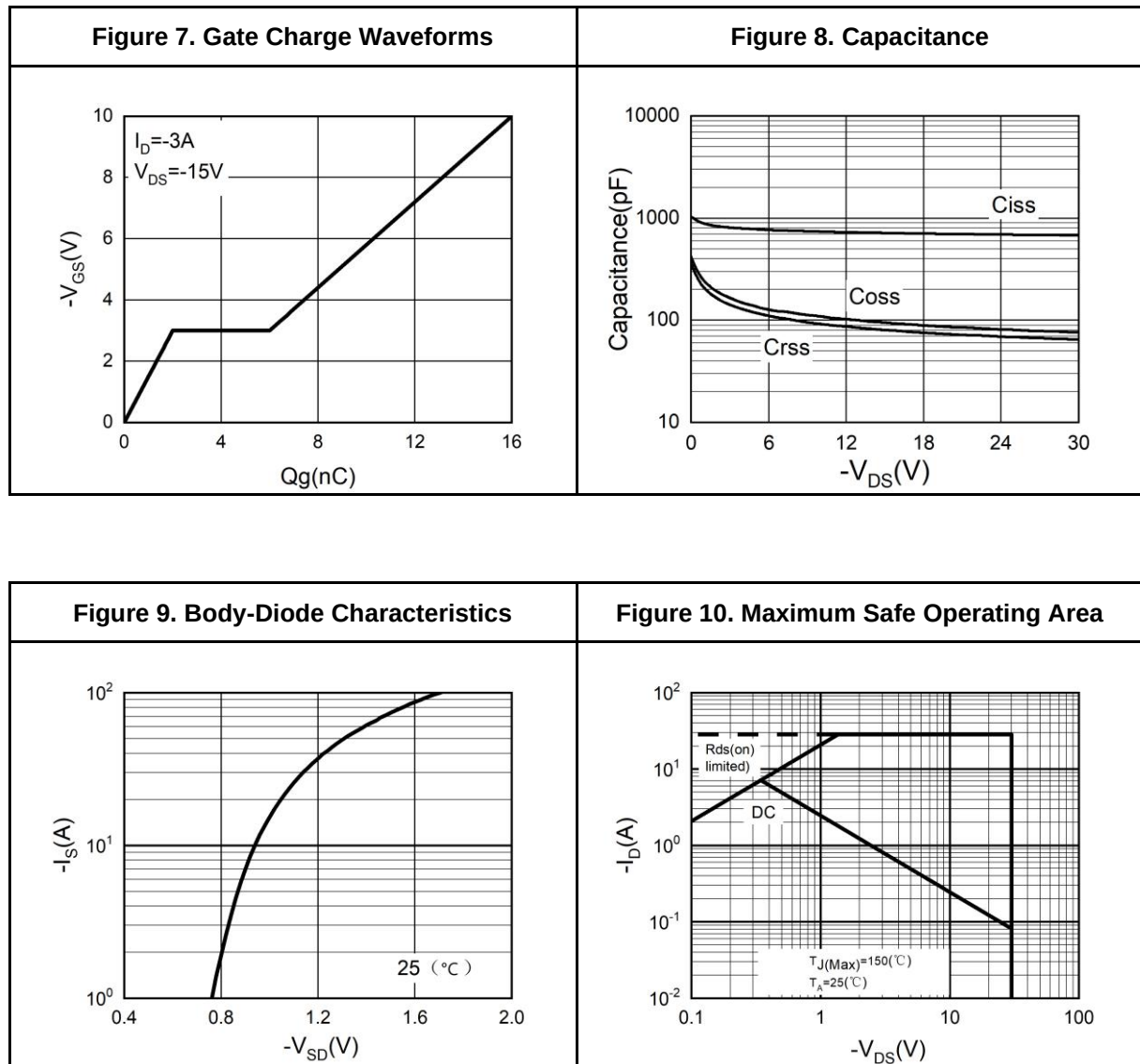
P-Channel Typical Electrical And Thermal Characteristics (Curves)





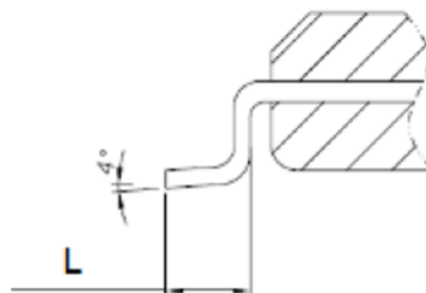
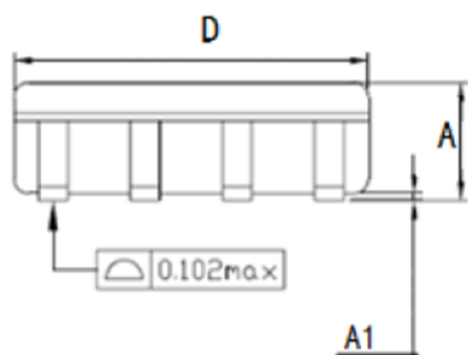
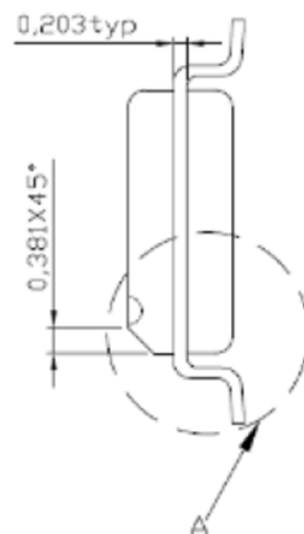
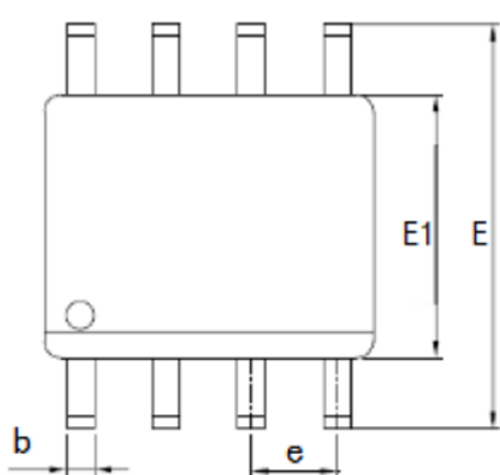
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P-Channel Typical Electrical And Thermal Characteristics (Curves)





SOP-8 Package Information



A 局部放大

Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max
A	1.35	1.55	1.75
A1	0.1	0.15	0.2
b	0.346	0.406	0.466
D	4.8	4.89	4.98
E	5.75	6.00	6.25
E1	3.81	3.90	3.99
e	1.27TYP		
L	0.406	0.838	1.27



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